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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE (211.004-US)

In re Application of: FERRANT ET AL.

U.S. Application Serial No: 10/840,009

U.S. Filing Date: MAY 6, 2004

Title: SEMICONDUCTOR MEMORY DEVICE AND

METHOD OF OPERATING SAME

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Group Art Unit: 2818

Examiner:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Bcx 1450, Alexandria, VA 22313-1450 on Alexandria, VA

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(person signing this certificate)

Signature



SECOND INFORMATION DISCLOSURE STATEMENT

Dear Sir.

Submitted herewith are seven (7) sheets of modified Form PTO-1449. A copy of each document identified on the Form PTO-1449 is also submitted.

It is respectfully requested that the Examiner make his/her consideration of these documents formally of record with the initial Office Action.

Respectfully submitted,

Date: August 11, 2004

Neil A. Steinberg Reg. No. 34,735

650-968-8079



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE (211.004-US)

APPLICANT: Ferrant et al.

Filed: May 6, 2004

SER!AL NO.: 10/840,009 TITLE: Semiconductor Memory Device and Method of Operating Same

RECEIPT OF THE FOLLOWING PAPERS IS ACKNOWLEDGED

1. Second Information Disclosure Statement (1 page + Modified Form-PTO-1449 (7 pages) + Retendes cited therein)

DATE: August 11, 2004

[Check No. N/A]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE (211.004-US)

In re Application of: FERRANT ET AL.

U.S. Application Serial No: 10/840,009

U.S. Filing Date: MAY 6, 2004

Title: SEMICONDUCTOR MEMORY DEVICE AND

METHOD OF OPERATING SAME

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Group Art Unit: 2818

Examiner:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on America, 2004

Michies (nerson signing this certificate)

Signature



FOURTH INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Submitted herewith are five (5) sheets of modified Form PTO-1449. A copy of each document identified on the Form PTO-1449 is also submitted.

It is respectfully requested that the Examiner make his/her consideration of these documents formally of record with the initial Office Action.

Respectfully submitted.

Date: August 12, 2004

Neil A. Steinberg

Reg. No. 34,735 650-968-8079



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